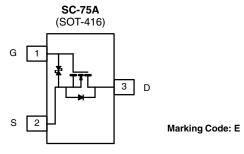


Vishay Siliconix

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS(min.)} (V)	R_{DS(on)} (Ω)	V _{GS(th)} (V)	I _D (mA)		
60	1.25 at V _{GS} = 10 V	1 to 2.5	330		



Ordering Information: Si1022R-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFETs
- Low On-Resistance: 1.25 Ω
- Low Threshold: 2.5 V
- Low Input Capacitance: 30 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid State Relays

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Error Voltage
- Small Board Area

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	v
	T _A = 25 °C	1-	330	
Continuous Drain Current ^a	T _A = 85 °C	ID	240	mA
Pulsed Drain Current ^a		I _{DM}	650	
Power Dissipation ^a	T _A = 25 °C	P _D	250	mW
	T _A = 85 °C	1 D	130	11100
Thermal Resistance, Maximum Junction-to-Ambienta		R _{thJA}	500	°C/W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C

Notes:

a. Surface mounted on FR4 board, power applied for t \leq 10 s.



RoHS COMPLIANT HALOGEN FREE

Si1022R

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 10 \mu A$	60			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 0.25 \text{ mA}$	1		2.5	v	
		$V_{DS} = 0 V, V_{GS} = \pm 10 V$			± 150		
Gate-Body Leakage	I _{GSS}	T _J = 85 °C			± 500		
		$V_{DS} = 0 V, V_{GS} = \pm 5 V$			± 20	nA	
		$V_{DS} = 50 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10		
Zero Gate Voltage Drain Current	I _{DSS}	T _J = 85 °C			100		
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	500			mA	
		V _{DS} = 7.5 V, V _{GS} = 10 V	800				
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 200 \text{ mA}$			3.0		
	R _{DS(on)}	T _J = 125 °C			5.0	0	
Drain-Source On-State Resistance ^a		V _{GS} = 10 V, I _D = 500 mA			1.25	Ω	
		T _J = 125 °C			2.25		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 200 mA	100			mS	
Diode Forward Voltage ^a	V _{SD}	V _{GS} = 0 V, I _S = 200 mA			1.3	V	
Dynamic ^b	•	•		•			
Input Capacitance	C _{iss}			30			
Output Capacitance	C _{oss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		6		pF	
Reverse Transfer Capacitance	C _{rss}			2.5		1	
Gate Charge	Qg	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 250 \text{ mA}, \text{ V}_{GS} = 4.5 \text{ V}$			0.6	nC	
Switching ^{b, c}		·					
Turn-On Time	t _(on)	V _{DD} = 30 V, R _L = 150 Ω,			25		
Turn-Off Time	t _(off)	$I_{\rm D}$ = 200 mA, $V_{\rm GEN}$ = 10 V, $R_{\rm g}$ = 10 Ω			35	ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. For DESIGN AID ONLY, not subject to production testing.

c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



25 °C

125 °C

5

6

4

15

75

T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

100

20

 $V_{GS} = 4.5 V$ at 200 mA

25

1200 1.0 6 V T_J = - 55 °C V_{GS} = 10 V thru 7 0.8 5 V 900 I_D - Drain Current (mA) I D - Drain Current (A) 0.6 600 4 V 0.4 300 0.2 3 V 0 0.0 2 3 4 5 0 1 2 3 0 1 V_{GS} - Gate-to-Source Voltage (V) V_{DS} - Drain-to-Source Voltage (V) **Output Characteristics Transfer Characteristics** 50 4.0 V_{GS} = 0 V f = 1 MHz 3.5 40 $R_{DS(on)}$ - On-Resistance (Ω) 3.0 C - Capacitance (pF) 2.5 30 $V_{GS} = 4.5 V$ C_{iss} 2.0 20 1.5 $V_{GS} = 10 V$ Coss 1.0 10 Crss 0.5 0.0 0 0 200 400 600 800 1000 0 5 10 I_D - Drain Current (mA) V_{DS} - Drain-to-Source Voltage (V) **On-Resistance vs. Drain Current** Capacitance 7 2.0 V_{DS} = 10 V I_D = 250 mA V_{GS} = 10 V at 500 mA 6 V_{GS} - Gate-to-Source Voltage (V) 1.6 R_{DS(on)} - On-Resistance 5 (Normalized) 1.2 4 3 0.8 2 0.4 1 0 0.0 0.0 0.1 0.2 0.3 0.4 0.5 0.6 - 50 - 25 0 25 50

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

Document Number: 71331 S10-2687-Rev. F, 22-Nov-10

Q_q - Total Gate Charge (nC)

Gate Charge

125

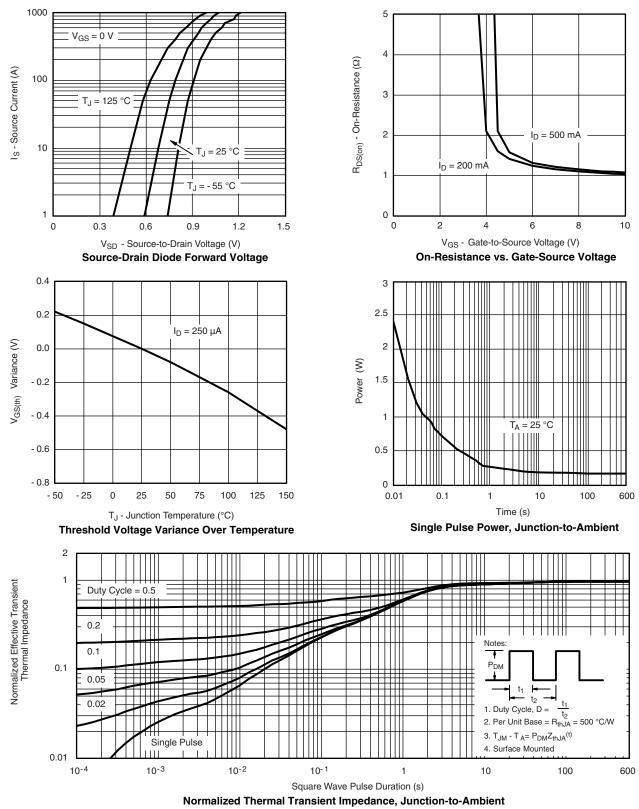
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Si1022R

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

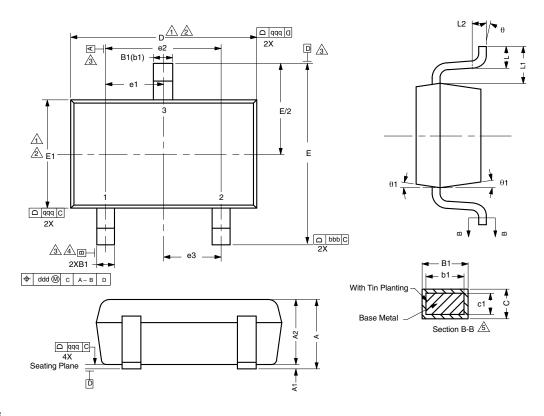


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Vishay Siliconix

SC-75A: 3 Leads



DWG: 5868

Notes

Dimensions in millimeters will govern.

- 1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- 2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- A Datums A, B and D to be determined 0.10 mm from the lead tip.

A Terminal positions are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ссс	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	NOTE
А	-	-	0.80	
A1	0.00	-	0.10	
A2	0.65	0.70	0.80	
B1	0.19	-	0.24	5
b1	0.17	-	0.21	
с	0.13	-	0.15	5
c1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e1	0.50 BSC			
e2	1.00 BSC			
e3	0.50 BSC			
L	0.15	0.205	0.30	
L1	0.40 ref.			
L2	0.15 BSC			
q	0°	-	8°	
q1	4°	-	10°	

C15-1445-Rev. F, 23-Nov-15

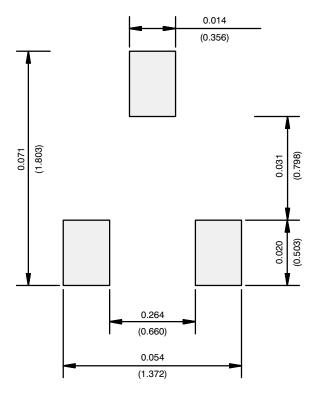
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Application Note 826

Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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